NSN 5961-01-295-5479

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-295-5479 **Inclosure Material:** Plastic **Overall Length:** Between 0.315 inches and 0.350 inches **Terminal Length:** 1.500 inches **Overall Diameter:** 0.220 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Mounting Method: Terminal Features Provided:** Burn in **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 7.5 reverse voltage, instantaneous and 8.33 breakdown voltage, dc and 9.21 breakdown voltage, dc **Current Rating Per Characteristic:** 10.00 milliamperes drain current pascal and 250.00 microamperes forward current, average outside diameter and 100.00 amperes source cutoff current universal **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector major **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 95105-204-0039-030 manufacturers specification control Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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